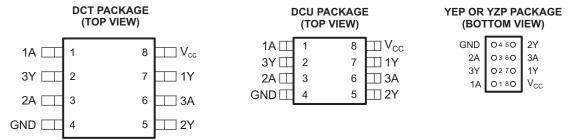
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FEATURES

- Available in the Texas Instruments
 NanoStar™ and NanoFree™ Packages
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 5.4 ns at 3.3 V
- Low Power Consumption, 10-μA Max I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) <0.8 V at V_{CC} = 3.3 V, T_A = 25°C

- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Partial-Power-Down Mode Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)



See mechanical drawings for dimensions.

DESCRIPTION/ORDERING INFORMATION

This triple Schmitt-trigger buffer is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC3G17 contains three buffers and performs the Boolean function Y = A. The device functions as three independent buffers but, because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

NanoStar[™] and NanoFree[™] package technology is a major breakthrough in IC packaging concepts, using the die as the package.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽²⁾
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Reel of 3000	SN74LVC3G17YEPR	C7
-40°C to 85°C	NanoFree [™] – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)		SN74LVC3G17YZPR	C7_
	SSOP - DCT	Reel of 3000	SN74LVC3G17DCTR	C17
	VSSOP - DCU	Reel of 3000	SN74LVC3G17DCUR	C17_

⁽¹⁾ Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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NanoStar, NanoFree are trademarks of Texas Instruments.

⁽²⁾ DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site.

DCU: The actual top-side marking has one additional character that designates the assembly/test site.

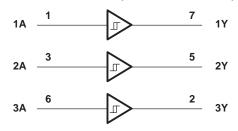
YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).



FUNCTION TABLE (EACH INVERTER)

INPUT A	OUTPUT Y
Н	Н
L	L

LOGIC DIAGRAM (POSITIVE LOGIC)



Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range (2)		-0.5	6.5	V
Vo	Voltage range applied to any output in the h	igh-impedance or power-off state ⁽²⁾	-0.5	6.5	V
Vo	Output voltage range ⁽²⁾⁽³⁾		-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		- 50	mA
Io	Continuous output current	,		±50	mA
	Continuous current through V _{CC} or GND			±100	mA
		DCT package		220	
θ_{JA}	Package thermal impedance (4)	DCU package		227	°C/W
		YEP/YZP package		102	
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

 ⁽³⁾ The value of V_{CC} is provided in the recommended operating conditions table.
 (4) The package thermal impedance is calculated in accordance with JESD 51-7.

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Recommended Operating Conditions⁽¹⁾

	·	·	MIN	MAX	UNIT	
V_{CC}	Supply voltage	Operating	1.65	5.5	V	
VI	Input voltage	·	0	5.5	V	
Vo	Output voltage		0	V_{CC}	V	
		V _{CC} = 1.65 V		-4		
		V _{CC} = 2.3 V		-8	mA	
I_{OH}	High-level output current	V -3 V		-16		
		V _{CC} = 3 V		-24		
		V _{CC} = 4.5 V		-32		
		V _{CC} = 1.65 V		4		
		V _{CC} = 2.3 V		8		
I_{OL}	Low-level output current	V 2.V		16	mA	
		$V_{CC} = 3 V$		24	24 32	
		V _{CC} = 4.5 V		32		
T _A	Operating free-air temperature		-40	85	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP ⁽¹⁾ MAX	UNIT		
		1.65 V	0.79	1.16			
V_{T+}		2.3 V	1.11	1.56			
Positive-going input threshold		3 V	1.5	1.87	V		
voltage		4.5 V	2.16	2.74			
		5.5 V	2.61	3.33			
		1.65 V	0.39	0.62			
V_{T-}		2.3 V	0.58	0.87			
Negative-going input threshold		3 V	0.84	1.14	V		
voltage		4.5 V	1.41	1.79			
		5.5 V	1.87	2.29			
ΔV_{T} Hysteresis $V_{T+} - V_{T-}$		1.65 V	0.37	0.62			
		2.3 V	0.48	0.77			
		3 V	0.56	0.87	V		
		4.5 V	0.71	1.04			
		5.5 V	0.71	1.11			
	$I_{OH} = -100 \mu A$	1.65 V to 5.5 V	$V_{CC} - 0.1$				
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2				
V	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9		V		
V_{OH}	$I_{OH} = -16 \text{ mA}$	3 V	2.4		V		
	$I_{OH} = -24 \text{ mA}$	3 V	2.3				
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8				
	$I_{OL} = 100 \mu A$	1.65 V to 5.5 V		0.1			
	I _{OL} = 4 mA	1.65 V		0.45			
V_{OL}	I _{OL} = 8 mA	2.3 V		0.3	V		
VOL	I _{OL} = 16 mA	3 V		0.4	V		
	I _{OL} = 24 mA	3 V		0.55			
	I _{OL} = 32 mA	4.5 V		0.55			
l _l	$V_I = 5.5 \text{ V or GND}$	0 to 5.5 V		±1	μΑ		
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0		±5	μΑ		
I _{CC}	$V_I = 5.5 \text{ V or GND}, I_O = 0$	1.65 V to 5.5 V		10	μΑ		
ΔI_{CC}	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V		500	μΑ		
C_{l}	$V_I = V_{CC}$ or GND	3.3 V		4	pF		

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

Switching Characteristics

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ or 50 pF (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} = 1 ± 0.2		V _{CC} = ± 0.3		V _{CC} = ± 0.5		UNIT	
	(INPOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
t _{pd}	Α	Υ	4.3	9.2	2	6.2	1.2	5.4	1	4.1	ns	



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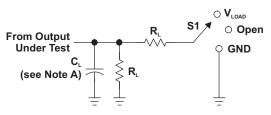
Operating Characteristics

 $T_A = 25^{\circ}C$

PARAMETER		DADAMETED	TEST CONDITIONS	V _{CC} = 1.8 V	$V_{CC} = 2.5 \text{ V}$	$V_{CC} = 3.3 \text{ V}$	$V_{CC} = 5 V$	UNIT
		PARAMETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	ONII
	C_{pd}	Power dissipation capacitance	f = 10 MHz	18	19	19	22	pF



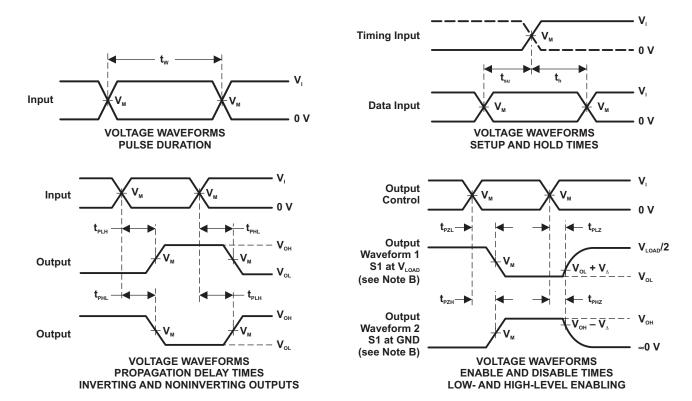
PARAMETER MEASUREMENT INFORMATION



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

	INPUTS			W		-	W
V _{cc}	V,	t,/t,	V _M	V _{LOAD}	C _L	R _⊾	V _Δ
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
2.5 V ± 0.2 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 M Ω	0.3 V
5 V ± 0.5 V	V _{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	15 pF	1 M Ω	0.3 V



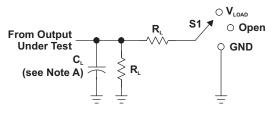
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{o} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms



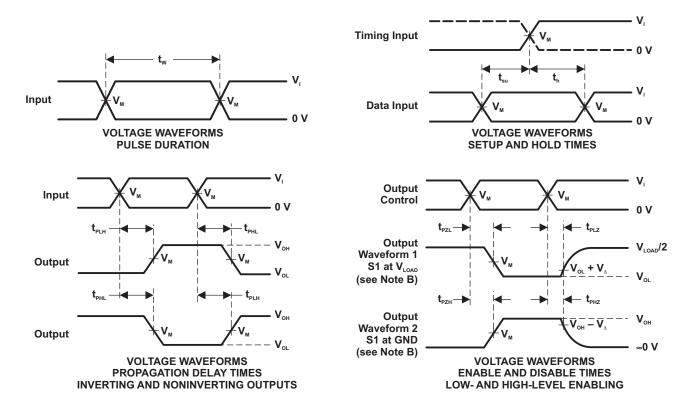
PARAMETER MEASUREMENT INFORMATION



TEST	S1
t _{PLH} /t _{PHL}	Open
t_{PLZ}/t_{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

V	INPUTS		V	V		D	.,	
V _{cc}	V,	t,/t,	V _M V _{LOAD}		C _L	R _L	$V_{\scriptscriptstyle \Delta}$	
1.8 V ± 0.15 V	V_{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V	
2.5 V ± 0.2 V	V_{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V	
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V	
5 V ± 0.5 V	V_{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V	



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_o = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and \dot{t}_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms





com 11-Oct-2006

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN74LVC3G17DCTR	ACTIVE	SM8	DCT	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC3G17DCTRE4	ACTIVE	SM8	DCT	8	3000	Pb-Free (RoHS)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC3G17DCUR	ACTIVE	US8	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC3G17DCURE4	ACTIVE	US8	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC3G17DCURG4	ACTIVE	US8	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74LVC3G17YEPR	NRND	WCSP	YEP	8	3000	TBD	SNPB	Level-1-260C-UNLIM
SN74LVC3G17YZPR	ACTIVE	WCSP	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion
- D. Falls within JEDEC MO-187 variation DA.

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



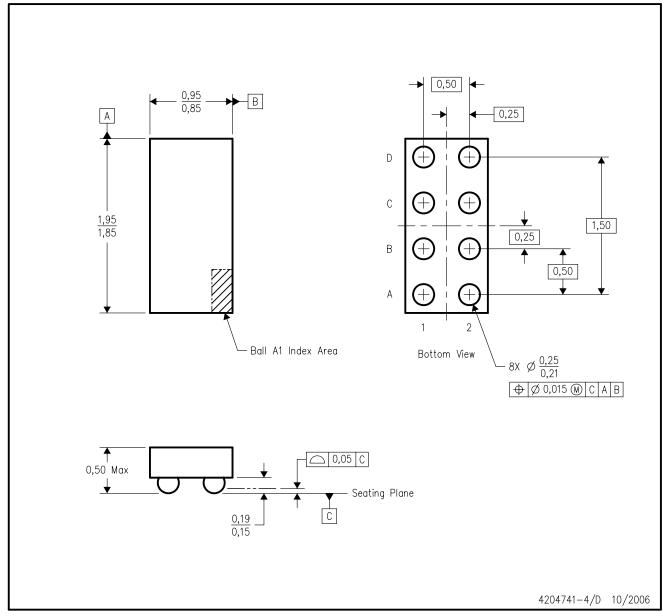
NOTES:

- : A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-187 variation CA.



YZP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

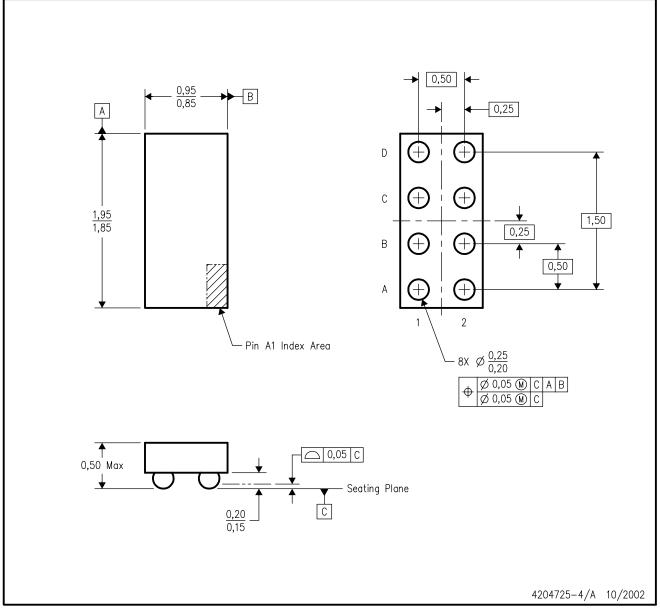
- B. This drawing is subject to change without notice.
- C. NanoFree $^{\text{TM}}$ package configuration.
- D. This package is lead—free. Refer to the 8 YEP package (drawing 4204725) for tin—lead (SnPb).

NanoFree is a trademark of Texas Instruments.



YEP (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. This package is tin-lead (SnPb). Refer to the 8 YZP package (drawing 4204741) for lead-free.

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